Growing Crystals of Topological Insulators

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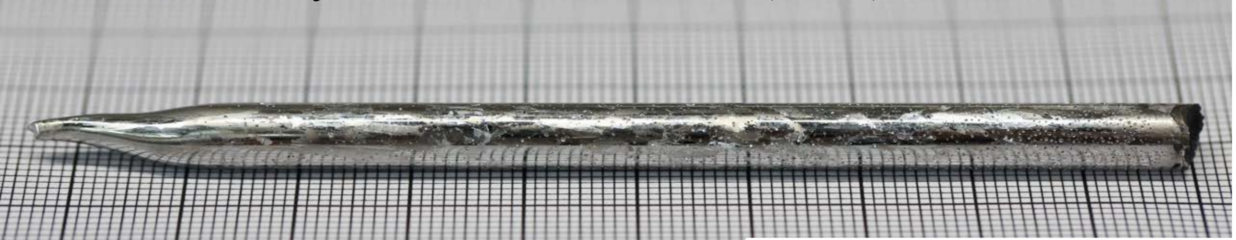
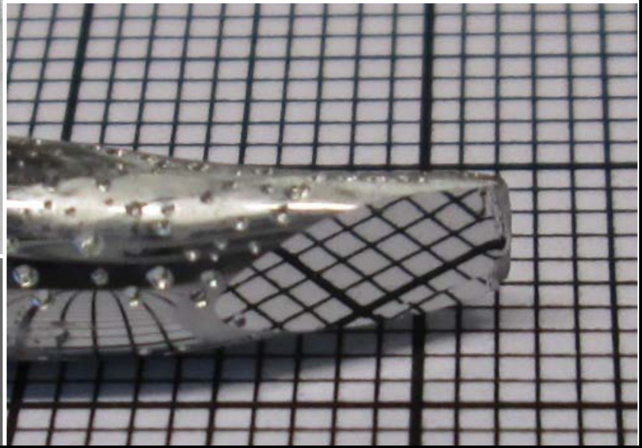
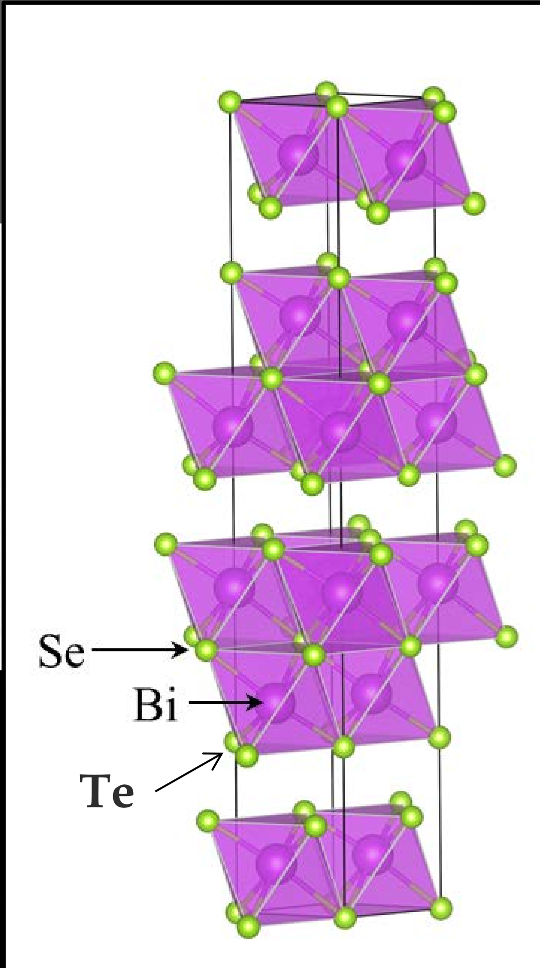




Studying the electronic properties of the surface states on Topological Insulators requires high quality bulk crystals. We have figured out the defect chemistry of these compounds and grown crystals by the Bridgman Stockbarger method.



Bi_2Te_2Se